

USB Type-C Power Delivery Controller

BM92A19MWV-Z

General Description

BM92A19MWV-Z is a full function USB Type-C Power Delivery (PD) controller that supports USB Power Delivery using baseband communication.

BM92A19MWV-Z includes support for the PD policy engine and communicates with an Embedded Controller or the SoC via host interface. It supports SOP, SOP' and SOP" signaling, allowing it to communicate with cable marker ICs, support alternate modes.

Features

- USB Type-C Specification Compatible
- USB PD Specification Compatible (BMC-PHY)
- Connected the Required Initial Voltage is 5 V
- Start of Automatic Power Receiving without Ext-MCU
- Two Power Path Control using N-ch MOSFET Drivers with Back Flow Prevention
- Type-C Cable Orientation Detection
- Built-in VCONN Switch and VCONN Controller
- Direct VBUS Powered Operation
- Initial Role is UFP Mode (Supports DFP/DRP mode)
- Supports Dead Battery Operation
- SMBus Interface for Host Communication

Key Specifications

- VBUS Voltage Range: 4.75 V to 20 V
- Power Consumption at Sleep Power: 0.4 mW (Typ)
- Operating Temperature Range: -30 °C to +105 °C

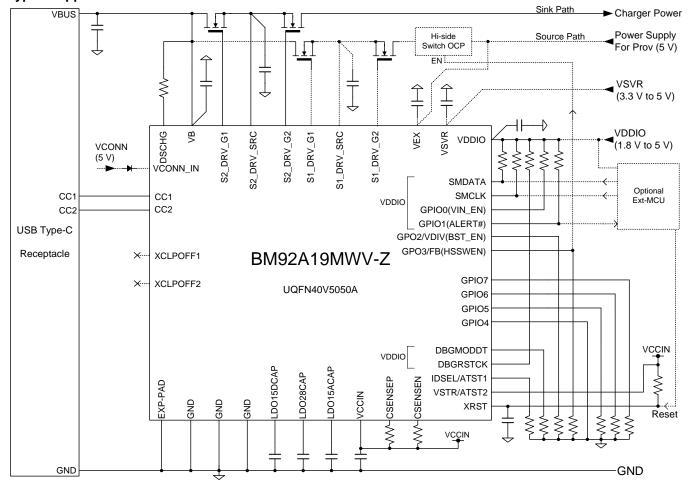
Applications

■ Consumer Applications: Laptop PCs, Tablet PCs

Package UQFN40V5050A W(Typ) x D(Typ) x H(Max) 5.00 mm x 5.00 mm x 0.90 mm



Typical Application Circuit



OProduct structure : Silicon monolithic integrated circuit OThis product has no designed protection against radioactive rays

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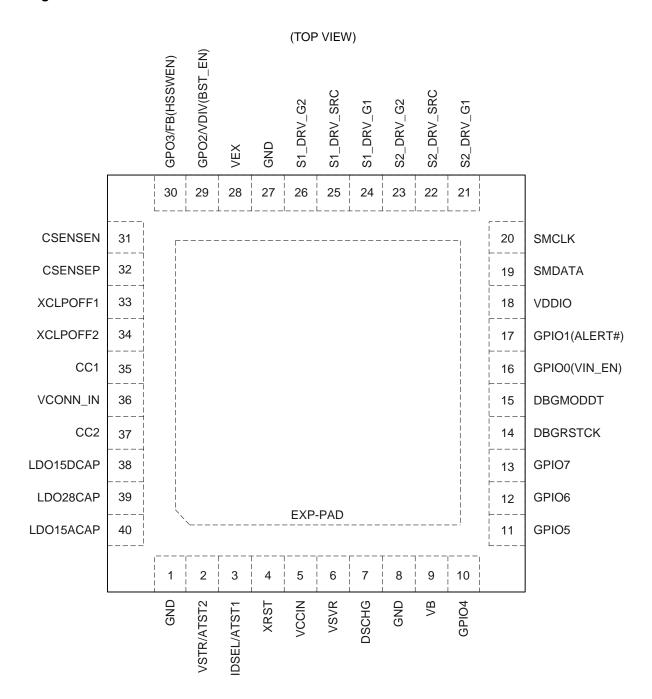
Notation

Category	Notation	Description					
	V	Volt (Unit of voltage)					
	Α	Ampere (Unit of current)					
	Ω, Ohm	Ohm (Unit of resistance)					
	F	Farad (Unit of capacitance)					
Unit	deg., degree	degree Celsius (Unit of temperature)					
Onit	Hz	Hertz (Unit of frequency)					
	s (lower case)	second (Unit of time)					
	min	minute (Unit of time)					
	b, bit	bit (Unit of digital data)					
	B, byte	1 byte=8 bits					
	M, mega-, mebi-	2 ²⁰ =1,048,576 (used with "bit" or "byte")					
	M, mega-, million-	10 ⁶ =1,000,000 (used with "Ω" or "Hz")					
	K, kilo-, kibi-	2 ¹⁰ =1,024 (used with "bit" or "byte")					
Unit prefix	k, kilo-	10^3 =1,000 (used with " Ω " or "Hz")					
Offic prefix	m, milli-	10 ⁻³					
	μ, micro-	10 ⁻⁶					
	n, nano-	10 ⁻⁹					
	p, pico-	10 ⁻¹²					
	xx h, xx H	Hexadecimal number. "x": any alphanumeric of 0 to 9 or A to F.					
Numeric value	xx b	Binary number; "b" may be omitted. "x": a number, 0 or 1 "_" is used as a nibble (4 bit) delimiter. (eg. "0011_0101b"="35 h")					
Address	#xx h	Address in a hexadecimal number. "x": any alphanumeric of 0 to 9 or A to F.					
Data	bit[n]	n-th single bit in the multi-bit data.					
Dala	bit[n:m]	Bit range from bit[n] to bit[m].					
	"H", High	High level (over V _{IH} or V _{OH}) of logic signal.					
Signal level	"L", Low	Low level (under V _{IL} or V _{OL}) of logic signal.					
	"Z", "Hi-Z"	High impedance state of 3-state signal.					

Reference

Name	Reference Document	Release Date	Publisher
USB Type-C	"USB Type-C Specification Release 1.1"	3.Apr.2015	USB.org
USB PD	"Power Delivery Specification Revision 2.0 Version 1.1"	7.May.2015	USB.org
SMBus	"System Management Bus (SMBus) Specification Version 2.0"	3.Aug.2000	System Management Implementers Forum

Pin Configuration



Pin Descriptions

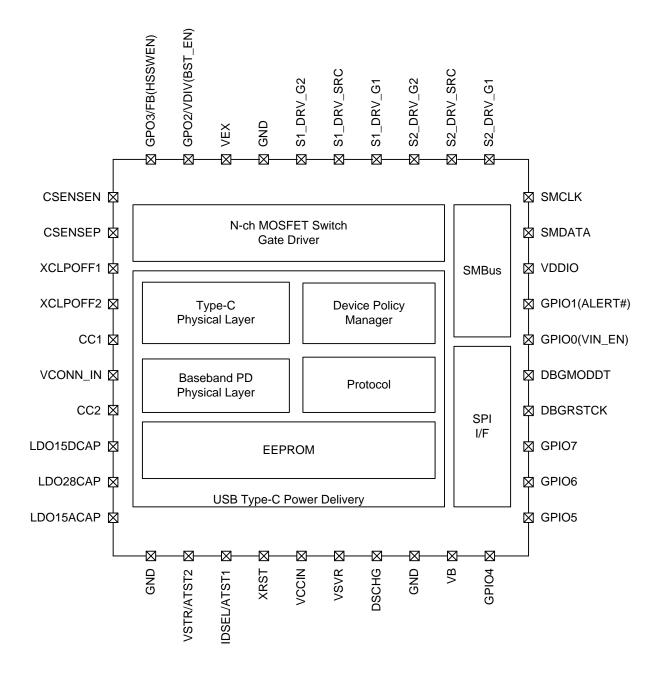
Pin No.	Pin Name	I/O	Type	Digital I/O Level	Description
1	GND	I	GND	-	Ground
2	VSTR/ATST2	Ю	Analog	-	Analog test/Debug pin
3	IDSEL/ATST1	I	Analog/ Digital	VCCIN	SMBus ID (device address) selection "H": 1A h, "L": 18 h/Debug pin
4	XRST	I	Digital	VCCIN	Digital block reset
5	VCCIN	0	Analog	-	Internal power supply (Need capacitor)
6	VSVR	I	Power	-	Power supply from SVR (5 V)
7	DSCHG	Ю	Analog	-	Discharge N-ch MOSFET drain
8	GND	I	GND	-	Ground
9	VB	I	Power	-	Power supply from VBUS
10	GPIO4	I	Digital	-	Mode fixation (Fix: L)
11	GPIO5	I	Digital	-	NC pin
12	GPIO6	I	Digital	-	NC pin
13	GPIO7	I	Digital	-	NC pin
14	DBGRSTCK	10	Digital	VDDIO	Test for logic
15	DBGMODDT	Ю	Digital	VDDIO	Test for logic
16	GPIO0(VIN_EN)	I	Digital	VDDIO	VIN_EN signal
17	GPIO1(ALERT#)	O ^(Note 1)	Digital	VDDIO	Alert signal
18	VDDIO	I	Power	-	Interface voltage
19	SMDATA	Ю	Digital	VDDIO	SMBus data
20	SMCLK	I	Digital	VDDIO	SMBus clock
21	S2_DRV_G1	0	Analog	-	Power path N-ch MOSFET gate control
22	S2_DRV_SRC	I	Analog	-	Power path N-ch MOSFET BG/source
23	S2_DRV_G2	0	Analog	-	Power path N-ch MOSFET gate control
24	S1_DRV_G1	0	Analog	-	Power path N-ch MOSFET gate control
25	S1_DRV_SRC	I	Analog	-	Power path N-ch MOSFET BG/source
26	S1_DRV_G2	0	Analog	-	Power path N-ch MOSFET gate control
27	GND	I	GND	-	Ground
28	VEX	I	Power	-	Extension power input
29	GPO2/VDIV(BST_EN)	0	Digital	VCCIN	Boost enable signal
30	GPO3/FB(HSSWEN)	0	Digital	VCCIN	Hi-side switch enable signal
31	CSENSEN	I	Analog/ Digital	VCCIN	Pin 29, 30 Configuration (Pin 31, 32)=(H, H): GPO mode
32	CSENSEP	I	Analog/ Digital	VCCIN	Pin 29, 30 Configuration (Pin 31, 32)=(H, H): GPO mode
33	XCLPOFF1	I	Analog/ Digital	VCCIN	Disable clamper of CC1 L: Dead-battery not support Open: Dead-battery support
34	XCLPOFF2	I	Analog/ Digital	VCCIN	Disable clamper of CC2 L: Dead-battery not support Open: Dead-battery support
35	CC1	Ю	Analog	-	Configuration channel 1 for Type-C
36	VCONN_IN	I	Analog	-	Input power for VCONN
37	CC2	Ю	Analog	-	Configuration channel 2 for Type-C
38	LDO15DCAP	0	Analog	-	Internal LDO 1.5 V for Digital (Need capacitor)
39	LDO28CAP	0	Analog	-	Internal LDO 2.8 V for Analog (Need capacitor)
40	LDO15ACAP	0	Analog	-	Internal LDO 1.5 V for Analog (Need capacitor)
-	EXP-PAD	-	-	-	The EXP-PAD connect to GND.

(Note 1) N-ch Open Drain

Block Diagram

BM92A19MWV-Z is a full function USB Type-C PD controller that supports USB Power Delivery using baseband communication. It is compatible with USB Type-C Specification and USB Power Delivery Specification.

BM92A19MWV-Z includes the following functional blocks: Type-C Physical Layer (baseband PHY), BMC encoder/decoder, USB PD Protocol engine, two N-ch MOSFET switch drivers to control each, OVP, Discharge FET and SMBus interface for communicating with the host controller. It requires an external embedded controller that includes Device Policy Manager and GPIOs for USB Type-C PD operation. BM92A19MWV-Z is able to operate independently in a dead battery condition where the embedded controller is not operational. BM92A19MWV-Z includes an EEPROM, enabling code updates via the SMBus interface during prototyping phase.



Absolute Maximum Ratings (Ta=25 °C)

Parameter	Symbol	Rating	Unit	Conditions
Maximum Supply Voltage1 (VB, VEX, DSCHG, S2_DRV_G1, S2_DRV_G2, S2_DRV_SRC, S1_DRV_G1, S1_DRV_SRC, S1_DRV_G2)	V _{IN1}	-0.3 to +28	V	(Note 2)
Maximum Supply Voltage2 (VDDIO, VSVR, DBGRSTCK, DBGMODDT, GPIO0, GPIO1, SMDATA, SMCLK, XRST, VCONN_IN, VSTR/ATST2, IDSEL/ATST1, VCCIN, GPIO4, GPIO5, GPIO6, GPIO7, GPO2/VDIV, GPO3/FB, CSENSEN, CSENSEP, XCLPOFF1, XCLPOFF2, CC1, CC2, LDO28CAP)	V _{IN2}	-0.3 to +6.5	V	-
Maximum Supply Voltage3 (LDO15DCAP, LDO15ACAP)	V_{IN3}	-0.3 to +2.1	V	-
Maximum Different Voltage (S2_DRV_G1 - S2_DRV_SRC, S2_DRV_G2 - S2_DRV_SRC, S1_DRV_G1 - S1_DRV_SRC, S1_DRV_G2 - S1_DRV_SRC)	V _{DIFF}	-0.3 to +6.5	V	-
Maximum Junction Temperature	Tjmax	150	°C	-
Storage Temperature Range	Tstg	-55 to +150	°C	-

Caution 1: Operating the IC over the absolute maximum ratings may damage the IC. The damage can either be a short circuit between pins or an open circuit between pins and the internal circuitry. Therefore, it is important to consider circuit protection measures, such as adding a fuse, in case the IC is operated over the absolute maximum ratings.

Caution 2: Should by any chance the maximum junction temperature rating be exceeded the rise in temperature of the chip may result in deterioration of the properties of the chip. In case of exceeding this absolute maximum rating, design a PCB with thermal resistance taken into consideration by

increasing board size and copper area so as not to exceed the maximum junction temperature rating.

(Note 2) The DSCHG pin connects more than 1 k Ω for current limiting.

Thermal Resistance^(Note 3)

Parameter	Symbol	Thermal Re	Unit	
		18(11010 0)	2s2p ^(Note 6)	
UQFN40V5050A				
Junction to Ambient	θ_{JA}	125.0	43.0	°C/W
Junction to Top Characterization Parameter ^(Note 4)	Ψ_{JT}	21	14	°C/W

⁽Note 3) Based on JESD51-2A(Still-Air).

(Note 4) The thermal characterization parameter to report the difference between junction temperature and the temperature at the top center of the outside surface of the component package.

(Note 5) Using a PCB board based on JESD51-3. (Note 6) Using a PCB board based on JESD51-5, 7

Layer Number of Measurement Board	Material	Board Size
Single	FR-4	114.3 mm x 76.2 mm x 1.57 mmt

Тор					
Copper Pattern	Thickness				
Footprints and Traces	70 µm				

	Layer Number of	Material	Board Size		Thermal Via ^{(r}	iote 7)
	Measurement Board	Material	Board Size		Pitch	Diameter
	4 Layers	FR-4	114.3 mm x 76.2 mm	x 1.6 mmt	1.20 mm	Ф0.30 mm
Ī	Тор		2 Internal Laye	ers	Bottom	
Ī	Copper Pattern	Thickness	Copper Pattern Thickne		Copper Pattern	Thickness
Ī	Footprints and Traces	70 um	74.2 mm x 74.2 mm	35 um	74.2 mm x 74.2 mm	70 um

(Note 7) This thermal via connects with the copper pattern of all layers.

Recommended Operating Conditions

Item	Cumbal	Limit			Unit	Conditions
	Symbol	Min	Тур	Max	Offic	Conditions
VB, VEX Voltage	V_B,V_{EX}	4.75	-	20	V	USB VBUS voltage
VSVR Voltage	V_{SVR}	3.1	-	5.5	V	-
VDDIO Voltage	V_{DDIO}	1.7	-	5.5	V	-
VCONN_IN Input Voltage	V_{CONN}	4.75	5.0	5.5	V	-
Operating Temperature	Topr	-30	+25	+105	°C	-

Electrical Characteristics

1. Internal Memory Cell Characteristics

 $(V_B=V_{EX}=4.75 \text{ V to } 20 \text{ V}, V_{SVR}=3.1 \text{ V to } 5.5 \text{ V})$

Item	Limit			Unit	Conditions	
item	Min	Тур	Max	Offic	Conditions	
Data Rewriting Number ^(Note 8)	1000	-	-	time	Ta≤25 °C	
	100	-	-	time	Ta≤105 °C	
Data Retention Life ^(Note 8)	20	-	-	year	Ta≤25 °C	
Data Retention Life	10	-	-	year	Ta≤105 °C	

Caution: Customer is permitted to rewrite EEPROM on BM92A19MWV-Z only in case of being provided technical support from ROHM. (Note 8) Not 100% tested.

2. Circuit Power Characteristics

(Ta=25 °C, V_{SVR}=V_{DDIO}=3.3 V, VB=VEX=Open)

Item	Limit			Unit	Conditions	
item	Min	Тур	Max	Offic	Conditions	
Sleep Power	-	0.4	-	mW	(Note 9)	
Standby Power	-	3.5	-	mW	(Note10)	

(Note 9) Sleep power: Power consumption at unattached plug. (Note 10) Standby power: Power consumption at attached plug.

Electrical Characteristics - continued

3. Digital Pin DC Characteristics

(Ta=25 °C, V_{SVR}=V_{DDIO}=3.3 V, VCCIN=VSVR, VB=VEX=Open)

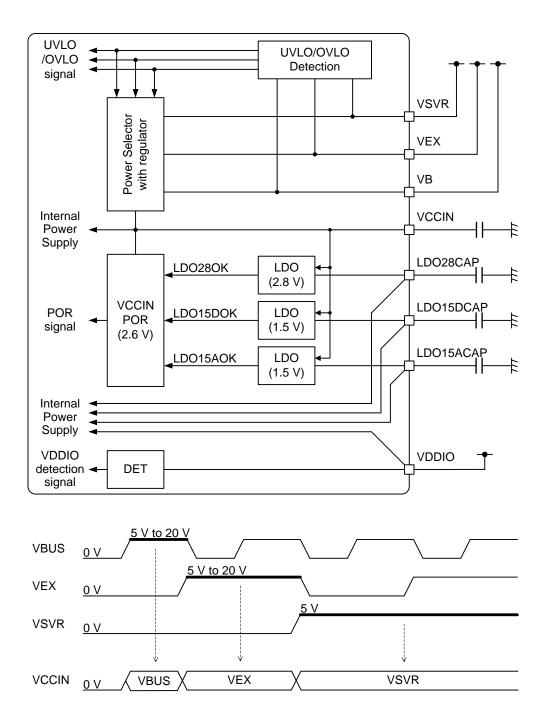
Item		Symbol			Lloit	Comment			
item	Symbol	Min	Тур	Max	Unit	Comment			
/DDIO Power Pin: GPIO0, GPIO1, SMDATA, SMCLK									
Input "H" Level	V _{IH1}	0.8x V _{DDIO}	-	V _{DDIO} + 0.3	V	-			
Input "L" Level	V _{IL1}	-0.3	-	0.2× V _{DDIO}	V	-			
Input Leak Current	I _{IC1}	-5	0	+5	μΑ	Power: VDDIO			
Output Voltage when "H"	V _{OH1}	0.7x V _{DDIO}	-	-	V	Source=1 mA			
SMDATA Pin "L" Level Voltage (SMDATA)	V _{OL_SMDATA}	-	-	0.4	V	Sink=350 µA Max.			
Output Voltage when "L" (GPIO0, GPIO1)	V _{OL1}	-	-	0.3	V	Sink=1 mA			
VCCIN Power Pin: XRST, GPO2, G	PO3, GPIO4, GI	PIO5, GPIO	6, GPIO7						
Input "H" Level	V _{IH2}	0.8x V _{CCIN}	-	V _{CCIN} + 0.3	V	-			
Input "L" Level	V _{IL2}	-0.3	•	0.2× V _{CCIN}	V	-			
Input Leak Current	I _{IC2}	-5	0	+5	μΑ	Power: VCCIN			
Output Voltage when "H" (GPIOs)	V _{OH2}	0.7× V _{CCIN}	-	-	V	Source=1 mA			
Output Voltage when "L" (GPIOs)	V _{OL2}	-	-	0.3	V	Sink=1 mA			

Electrical Characteristics - continued

4. Power Supply Management

BM92A19MWV-Z has a power selector. It selects the lowest power supply voltage from the VSVR, VEX or VB pins for low power consumption. Internal Power Supply (the VCCIN pin) gives priority in order of the VSVR, VEX and VB pins. The VCCIN pin supplied from the power selector is used to BM92A19MWV-Z main power source. LDOs (for internal only) are supplied from the VCCIN pin, and output each internal supply voltage.

Each power supply input has UVLO and OVLO. And POR (power on reset) signal is generated from detection of LDO28OK, LDO15DOK and LDO15AOK signals, and the VCCIN pin.



4. Power Supply Management - continued

Item		Limit			2			
		Тур	Max	Unit	Comment			
Unless otherwise specified Ta=25 °C, V _{GND} =0 V,		1						
C _{VCCIN} =4.7 μF (Ceramic), C _{LDO28} =C _{LDO15D} =C _{LDO15A} =1 μF (Ceramic) Input Analog Pins: VSVR, VEX, VB								
UVLO Rising Threshold Voltage 1	-	2.8	-	V	VSVR			
UVLO Rising Threshold Voltage 2	-	3.5	-	V	VEX, VB			
UVLO Falling Threshold Voltage	-	2.7	-	V	VSVR, VEX, VB			
OVLO Rising Threshold Voltage	-	6.4	-	V	VSVR			
OVLO Rising Threshold Voltage	-	28	-	V	VEX, VB			
OVLO Hysteresis Voltage 1	-	240	-	mV	VSVR			
OVLO Hysteresis Voltage 2	-	920	-	mV	VEX, VB			
Power ON Reset Threshold Voltage	-	2.6	-	V	VCCIN			
VDDIO Detection Voltage	1.7	-	-	V	For dead battery operation			
LDO28CAP Output Voltage	-	2.8	-	V	No Load, V _{SVR} =5 V			
LDO15DCAP Output Voltage	-	1.5	-	V	No Load, V _{SVR} =5 V			
LDO15ACAP Output Voltage	-	1.5	-	V	No Load, V _{SVR} =5 V			

Electrical Characteristics - continued

5. CC PHY

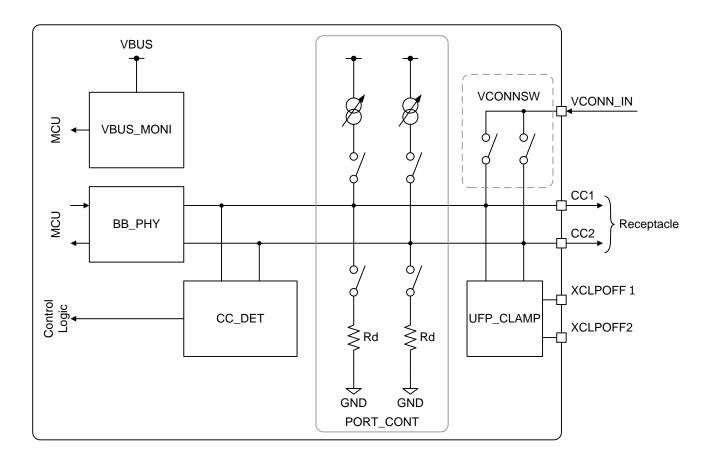
CC_PHY has below functions of USB Type-C (Refer to USB Type-C Specification):

Defining Port Mode: DFP/UFP/DRP DFP-to-UFP Attach/Detach Detection Plug Orientation/Cable Twist Detection

USB Type-C VBUS Voltage Detection and Usage

VCONN (Supply for SOP') Control

Baseband Power Delivery Communication (BBPD Communication)



PORT_CONT

This block chose the port mode according to the setting from MCU.

DFP mode: Variable current source is connected to the CC1 and CC2 pin. These currents of each mode

are Default Current, Medium Current and High Current. UFP mode: Pull-down resistor is connected to the CC1 and CC2 pin.

DRP mode: Changing DFP and UFP is repeated frequently.

CC_DET

CC_DET has functions of "Attach/Detach Detection", "Plug Orientation/Cable Twist Detection", "Discovery and detect extension mode" and "USB Type-C VBUS Current Detection".

Attach/Detach is detected with monitoring voltage of the CC1 and CC2 pin. When the voltage of the CC1 and CC2 pin become under a threshold voltage at DFP, attach is detected. Oppositely, when the voltage of the CC1 and CC2 pin become over a threshold voltage, detach is detected. When the voltage of the CC1 and CC2 pin become over a threshold voltage at UFP, attach is detected.

5. CC_PHY - continued

Plug orientation and cable twist is detected from the relationship of the CC1 and CC2 pins.
UFP can detect the maximum current of the power source by monitoring the voltage of the CC1 and CC2 pin.

UFP_CLAMP

Clamp is used for UFP emulation at dead-battery condition.

VBUS_MONI

UFP detect Attach/Detach by existence of VBUS voltage. VBUSDET detects Attach when VBUS voltage over the threshold voltage. And it detects Detach when VBUS under the threshold voltage.

VCONNSW

VCONNSW is the power switch for VCONN source. It has OCP function.

BB_PHY

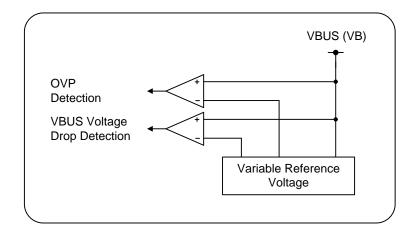
If Type-C controller supports BBPD, the CC1 and CC2 pin can output BBPD communication signal.

ltom	Limit			Unit	Comment			
Item		Тур	Max	Unit	Comment			
[PORT_CONT Characteristics] Unless otherwise specified Ta=25 °C, V _{SVR} =V _B =V _{CONN_IN} =5 V, V _{DDIO} =3.3 V, V _{GND} =0 V, C _{VCCIN} =4.7 µF(Ceramic), C _{LDO28} =C _{LDO15D} =C _{LDO15A} =1 µF(Ceramic) Input Analog Pins: CC1, CC2								
Default Current	64	80	96	μA	-			
Medium Current	166	180	194	μA	-			
High Current	304	330	356	μA	-			
Pull Down Resistor	4.6	5.1	5.6	kΩ	-			
[UFP_CLAMP Characteristics] Unless otherwise specified Ta=25 °C, $V_{SVR}=V_B=V_{CONN_IN}=5$ V, $V_{DDIO}=3.3$ V, $V_{GND}=0$ V, $C_{VCCIN}=4.7$ μ F(Ceramic), $C_{LDO28}=C_{LDO15D}=C_{LDO15A}=1$ μ F(Ceramic) Input Analog Pins: CC1, CC2								
CCx Pin Input Impedance	126	-	-	kΩ	-			
CCx Clamp Voltage	0.7	-	1.3	V	Pull up=64 μA to 356 μA			
[VBUS_MONI] Unless otherwise specified $ Ta=25~^{\circ}C,~V_{SVR}=V_{CONN_IN}=5~V,~V_{DDIO}=3.3~V,~V_{GND}=0~V,~C_{VCCIN}=4.7~\mu F(Ceramic),~C_{LDO28}=C_{LDO15D}=C_{LDO15A}=1~\mu F(Ceramic)~Input~Analog~Pin:~VB$								
VBUS Presence Detection Level	-	3.42	-	V	-			
[VCONNSW] Unless otherwise specified								
VCONN_IN to CCx Resistance	-	-	500	mΩ	-			
Overcurrent Protection Level	1.1	-	-	Α	-			

Electrical Characteristics - continued

6. Voltage Detection

VDET Block detects the voltage level of VB. It can detect follow conditions: OVP (Over Voltage Protection) Detection VBUS Voltage Drop Detection

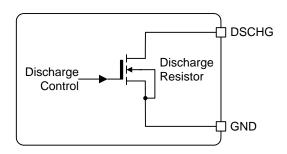


Itom		Limit			Comment			
Item	Min	Тур	Max	Unit	Comment			
Unless otherwise specified								
Ta=25 °C, V _{SVR} =V _{CONN IN} =5 V, V _{DDIO} =3.3 V, V _{GND} =0 V,								
C _{VCCIN} =4.7 μF(Ceramic), C _{LDO28} =C _{LDO15D} =C _{LDO15A} =1 Input Analog Pin: VB	μF(Cera	mic)						
Over Voltage Protection Detection Rate +15 +20 +25 % (Note 11)								
VBUS Voltage Drop Detection Rate	-30	-25	-20	%	(Note 11)			

(Note 11) Reference value is USB PD negotiation voltage.

7. VBUS Discharge

FET switch is prepared for VBUS discharging.

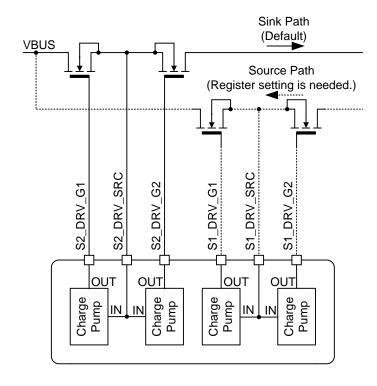


Item		Limit			Commont	
		Тур	Max	Unit	Comment	
Unless otherwise specified Ta=25 °C, $V_{SVR}=V_B=V_{CONN_IN}=5$ V, $V_{DDIO}=3.3$ V, $V_{GND}=0$ V, $C_{VCCIN}=4.7~\mu F(Ceramic)$, $C_{LDO28}=C_{LDO15D}=C_{LDO15A}=1~\mu F(Ceramic)$ Input Analog Pin: DSCHG						
FET Switch ON Resistance	-	25	-	Ω	-	

Electrical Characteristics - continued

8. Power FET Gate Driver

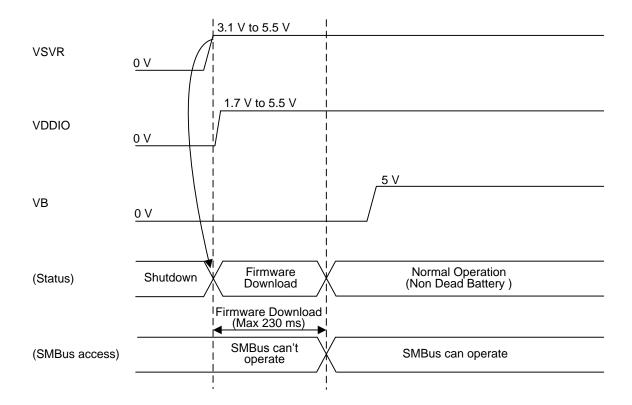
FET Gate Driver is the external N-ch MOSFET switch driver for power line switch.



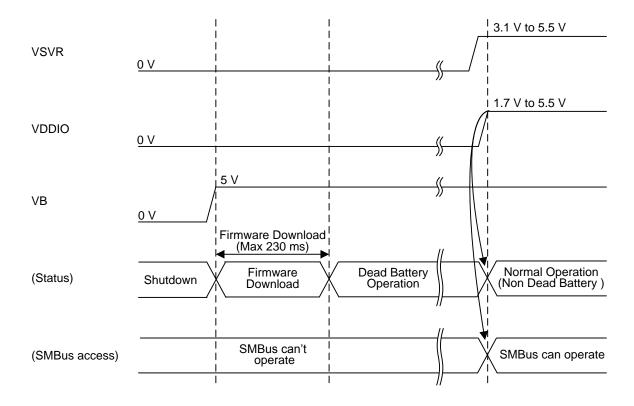
Itom		Limit			Comment
Item	Min	Тур	Max	Unit	Comment
Unless otherwise specified Ta=25 °C, $V_{SVR}=V_{B}=V_{CONN_IN}=5$ V, $V_{DDIO}=3.3$ V, $V_{GND}=0$ V, $C_{VCCIN}=4.7$ $\mu F(Ceramic)$, $C_{LDO28}=C_{LDO15D}=C_{LDO15A}=1$ $\mu F(Ceramic)$ Input Analog Pins: S1_DRV_SRC=S2_DRV_SRC=0 V Output Analog Pins: S1_DRV_G1, S1_DRV_G2, S2_DRV_G1, S2_DRV_G2					
N-ch MOSFET Control Voltage Between Gate and Source	-	6.0	-	V	S1_DRV_G1 - S1_DRV_SRC S1_DRV_G2 - S1_DRV_SRC S2_DRV_G1 - S2_DRV_SRC S2_DRV_G2 - S2_DRV_SRC

Timing Chart

1. Power On Sequence (Non Dead Battery Operation)

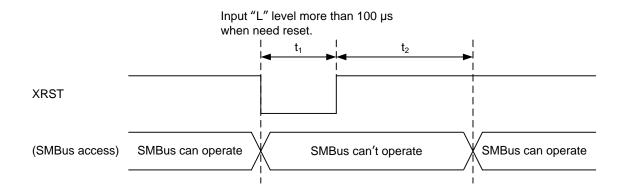


2. Power On Sequence (Dead Battery Operation)



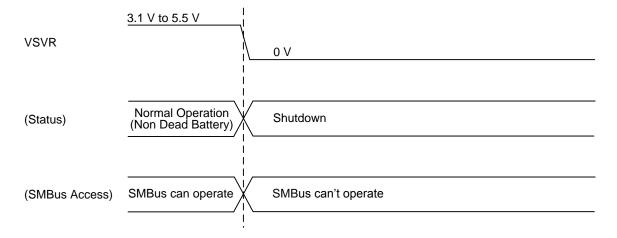
Timing Chart - continued

3. Reset Timing

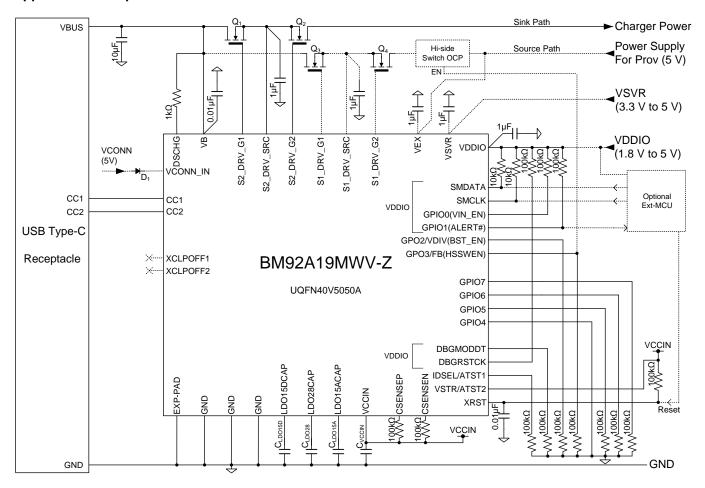


Itom	Cymbol		Limit		Unit	Comment
Item	Symbol	Min	Тур	Max		
XRST Minimum "L" Level Pulse	t ₁	100	-	-	μs	-
SMBus Access Start After XRST Release	t ₂	230	-	-	ms	-

4. Power Off Sequence



Application Example

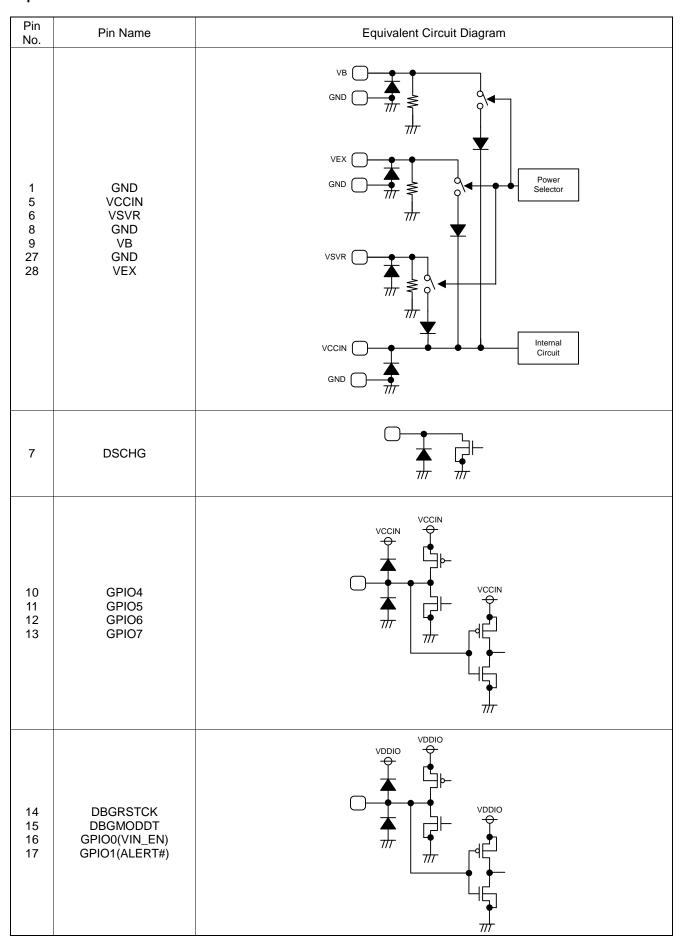


Selection of Components Externally Connected

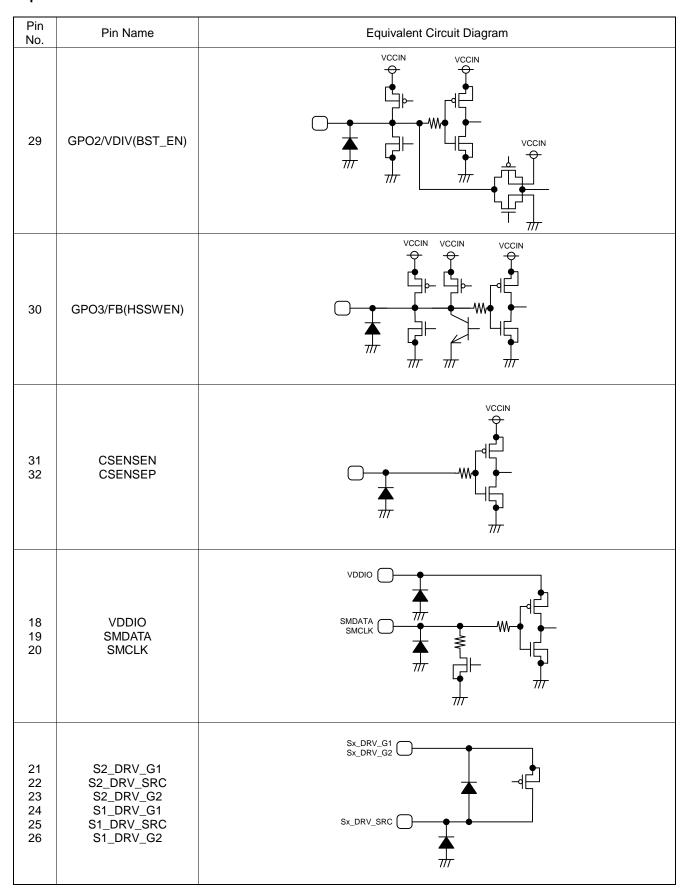
Item	Cymhol	Limit			Unit	Commont
item	Symbol	Min	Тур	Max	Offic	Comment
VCCIN Capacitance	C _{VCCIN}	0.60	4.7	10	μF	(Note 12)
LDO15ACAP Capacitance	C _{LDO15A}	0.47	1.0	2.2	μF	(Note 12)
LDO15DCAP Capacitance	C _{LDO15D}	0.47	1.0	2.2	μF	(Note 12)
LDO28CAP Capacitance	C _{LDO28}	0.47	1.0	2.2	μF	(Note 12)
Q ₁ , Q ₂ , Q ₃ , Q ₄ Gate-Source Capacitance	C _{Qx_gs}	470 p	-	0.5 μ	F	-

(Note 12) Use the ceramic capacitor which capacitance value to decrease by temperature characteristics and DC bias is larger than the minimum limit.

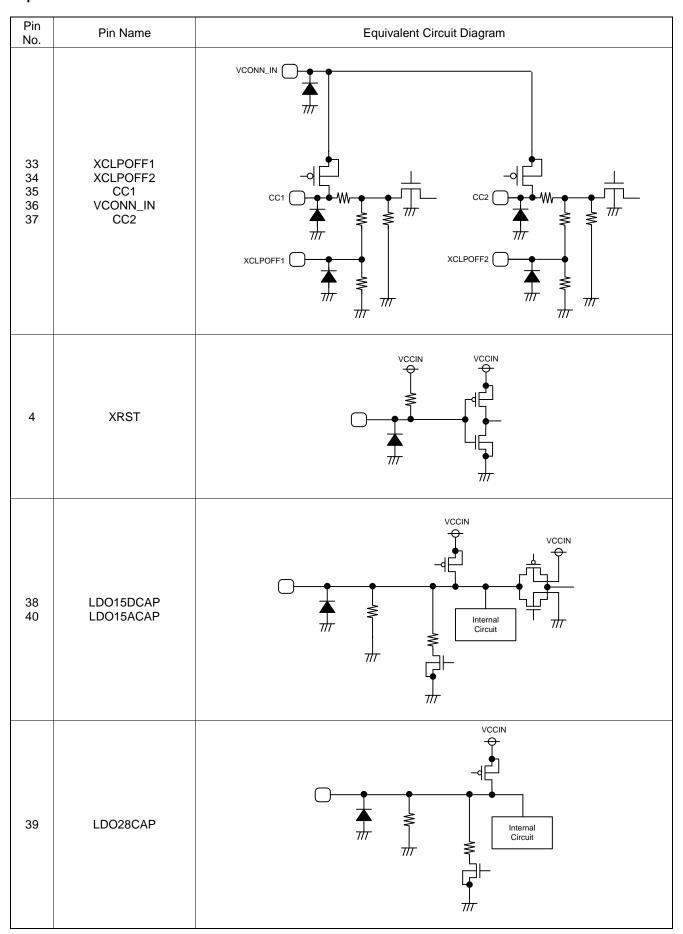
I/O Equivalence Circuit



I/O Equivalence Circuit - continued



I/O Equivalence Circuit - continued



I/O Equivalence Circuit - continued

Pin No.	Pin Name	Equivalent Circuit Diagram
2	VSTR/ATST2	VCCIN W
3	IDSEL/ATST1	VCCIN W W W

Register Initial Values

Firmware Information

Code	Command	Protocols	Data Size	Initial Values
4B h	Firmware Type (Vendor Specific)	Read Word	2	0901 h
4C h	Firmware Revision (Vendor Specific)	Read Word	2	179E h

Operational Notes

1. Reverse Connection of Power Supply

Connecting the power supply in reverse polarity can damage the IC. Take precautions against reverse polarity when connecting the power supply, such as mounting an external diode between the power supply and the IC's power supply pins.

2. Power Supply Lines

Design the PCB layout pattern to provide low impedance supply lines. Separate the ground and supply lines of the digital and analog blocks to prevent noise in the ground and supply lines of the digital block from affecting the analog block. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

3. Ground Voltage

Ensure that no pins are at a voltage below that of the ground pin at any time, even during transient condition.

4. Ground Wiring Pattern

When using both small-signal and large-current ground traces, the two ground traces should be routed separately but connected to a single ground at the reference point of the application board to avoid fluctuations in the small-signal ground caused by large currents. Also ensure that the ground traces of external components do not cause variations on the ground voltage. The ground lines must be as short and thick as possible to reduce line impedance.

5. Recommended Operating Conditions

The function and operation of the IC are guaranteed within the range specified by the recommended operating conditions. The characteristic values are guaranteed only under the conditions of each item specified by the electrical characteristics.

6. Inrush Current

When power is first supplied to the IC, it is possible that the internal logic may be unstable and inrush current may flow instantaneously due to the internal powering sequence and delays, especially if the IC has more than one power supply. Therefore, give special consideration to power coupling capacitance, power wiring, width of ground wiring, and routing of connections.

7. Testing on Application Boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.

Operational Notes - continued

8. Inter-pin Short and Mounting Errors

Ensure that the direction and position are correct when mounting the IC on the PCB. Incorrect mounting may result in damaging the IC. Avoid nearby pins being shorted to each other especially to ground, power supply and output pin. Inter-pin shorts could be due to many reasons such as metal particles, water droplets (in very humid environment) and unintentional solder bridge deposited in between pins during assembly to name a few.

9. Unused Input Pins

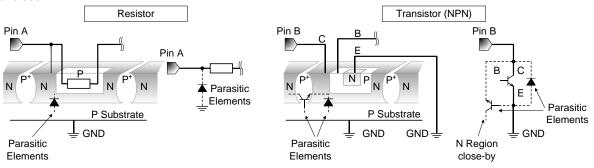
Input pins of an IC are often connected to the gate of a MOS transistor. The gate has extremely high impedance and extremely low capacitance. If left unconnected, the electric field from the outside can easily charge it. The small charge acquired in this way is enough to produce a significant effect on the conduction through the transistor and cause unexpected operation of the IC. So unless otherwise specified, unused input pins should be connected to the power supply or ground line.

10. Regarding the Input Pin of the IC

This IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of the P layers with the N layers of other elements, creating a parasitic diode or transistor. For example (refer to figure below):

When GND > Pin A and GND > Pin B, the P-N junction operates as a parasitic diode. When GND > Pin B, the P-N junction operates as a parasitic transistor.

Parasitic diodes inevitably occur in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Therefore, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.



11. Ceramic Capacitor

When using a ceramic capacitor, determine a capacitance value considering the change of capacitance with temperature and the decrease in nominal capacitance due to DC bias and others.

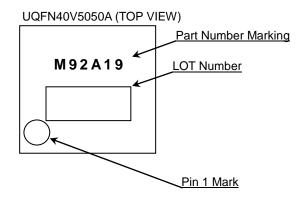
12. Over Current Protection Circuit (OCP)

This IC incorporates an integrated overcurrent protection circuit that is activated when the load is shorted. This protection circuit is effective in preventing damage due to sudden and unexpected incidents. However, the IC should not be used in applications characterized by continuous operation or transitioning of the protection circuit.

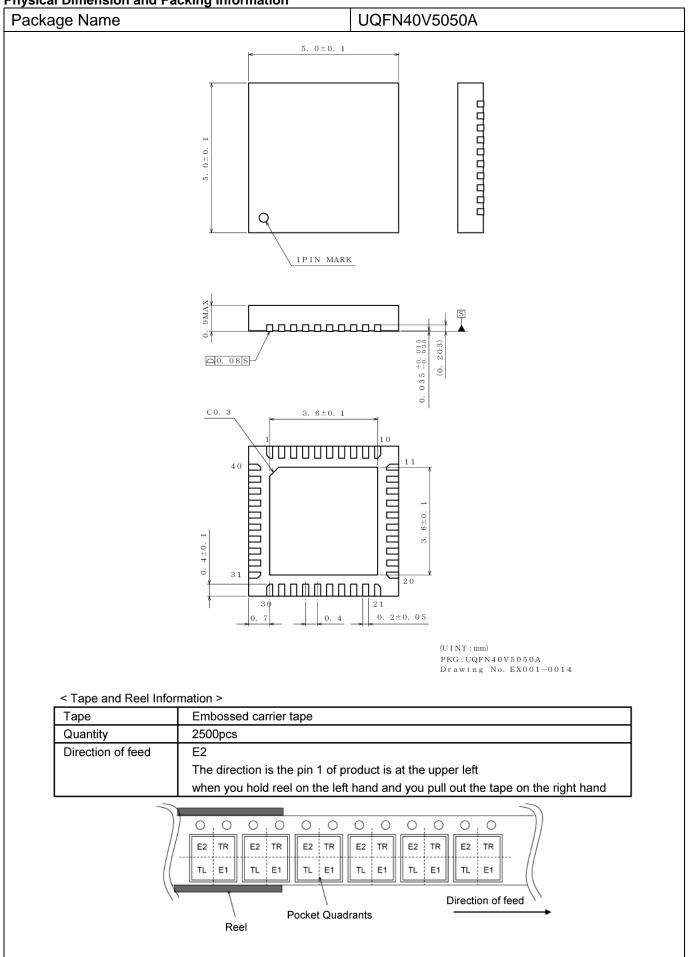
Ordering Information



Marking Diagrams



Physical Dimension and Packing Information



Revision History

Date	Revision	Changes
19.Jul.2018	001	New Release

Notice

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(Note1) Medical Equipment Classification of the Specific Applications

JÁPAN	USA	EU	CHINA	
CLASSIII	OL ACOM	CLASS II b	ОГУООШ	
CLASSIV	CLASSⅢ	CLASSIII	CLASSⅢ	

- 2. ROHM designs and manufactures its Products subject to strict quality control system. However, semiconductor products can fail or malfunction at a certain rate. Please be sure to implement, at your own responsibilities, adequate safety measures including but not limited to fail-safe design against the physical injury, damage to any property, which a failure or malfunction of our Products may cause. The following are examples of safety measures:
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 - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
 - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

Precautions Regarding Application Examples and External Circuits

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

Precaution for Electrostatic

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
 - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

Precaution for Product Label

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Precaution for Disposition

When disposing Products please dispose them properly using an authorized industry waste company.

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